



09-13-04

IPW

Express Mail No. EL963273053US
ELM/001 Cont. 14

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy
Application No. : 10/766,557 Confirmation No. : 3092
Filed : January 27, 2004
For : METHODS FOR MASKLESS LITHOGRAPHY
Examiner : Not yet assigned
Group Art Unit : 2812

New York, New York 10020
September 10, 2004

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97,
applicants wish to call the attention of the Examiner to the
following documents:

U.S. Patent Documents

Shibata	4,500,905	02/19/1985
Wang, et al.	4,892,753	01/09/1990
Kato, et al.	4,939,568	07/03/1990
Wang, et al.	5,000,113	03/19/1991
Linglain, et al.	5,240,458	08/31/1993
Bantien	5,259,247	11/09/1993
Fujii, et al.	RE 34,893	04/04/1995
Wang, et al.	RE 36,623	03/21/2000
Brix, et al.	6,087,284	07/11/2000
Momohara	6,518,073	02/11/2003

Foreign Patent Documents

Japan 04-196263 07/1992

Other Documents

Aboaf, J.A., "Stresses in SiO₂ Films Obtained from the Thermal Decomposition of Tetraethylorthosilicate - Effect of Heat Treatment and Humidity," J. Electrochem. Soc.: Solid State Science; 116(12): 1732-1736 (Dec. 1969).

Scheuerman, R.J., "Fabrication of Thin Dielectric Films with Low Internal Stresses," J. Vac. Sci. and Tech., 7(1): 143-146 (1970).

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Treichel, et al., "Planarized Low-Stress Oxide/Nitride Passivation for ULSI Devices," J. Phys IV, Colloq. (France), 1 (C2): 839-846 (1991).

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"Miniature Electron Microscopes Without Vacuum Pumps, Self-Contained, Microfabricated Devices with Short

"Working Distances, Enable Operation in Air," NASA Tech Briefs, 39-40 (1998).

Partial European Search Report for Application No. EP 02009643 (October 8, 2002).

Copies of the aforementioned documents, which are listed on the accompanying Form PTO-1449 (submitted in duplicate), are enclosed herewith.

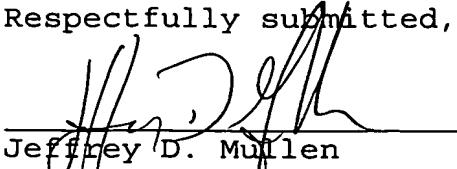
It is respectfully requested that these documents be (1) fully considered by the Patent and Trademark Office during examination of this application; and (2) printed on any patent which may issue on this application. Applicants request that a copy of Form PTO-1449, as considered and initialed by the Examiner, be returned with the next communication.

This Statement is being submitted more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97(b)(3), submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this Supplemental Information Disclosure Statement to Deposit Account No. 06-1075. A duplicate copy of this statement is transmitted herewith.

An early and favorable action is respectfully
requested.

Respectfully submitted,



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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ELM/001 Cont. 14	APPLN. NO. 10/766,557
O I P E SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT SEP 10 2004 JCC PATENT & TRADEMARK OFFICE 09C		APPLICANTS Glenn J. Leedy	CONF. NO. 3092
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	4,500,905	02/19/1985	Shibata	357	68	
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	5,000,113	03/19/1991	Wang, et al.	118	723	
	5,240,458	08/31/1993	Linglain, et al.	464	63	
	5,259,247	11/09/1993	Bantien	73	718	
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						YES	NO
	04-196,263	07/1992	Japan				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL	
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EXPRESS MAIL CERTIFICATION

"Express Mail" Mailing Label No. EL963273053US
Date of Deposit: September 10, 2004

I hereby certify that this certification and the following papers and fees:

1. Supplemental Information Disclosure Statement (in duplicate);
2. Form PTO-1449 (in duplicate);
3. Copies of twenty-two (22) cited references; and
4. Return postcard

are being deposited with the United States Postal Service "EXPRESS MAIL POST OFFICE TO ADDRESSEE" service under 37 C.F.R. § 1.10 on the date indicated above and are addressed to Mail Stop Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Name: Claire J. Saintil-van Goodman